PSRAM 2-Mbit (256K x 8) Pseudo Static RAM

Features

•Advanced low-power architecture
•High speed: 55 ns, 70 ns
•Wide voltage range: 2.7V to 3.3V
•Typical active current: 1 mA @ f = 1 MHz
•Low standby power
•Automatic power-down when deselected

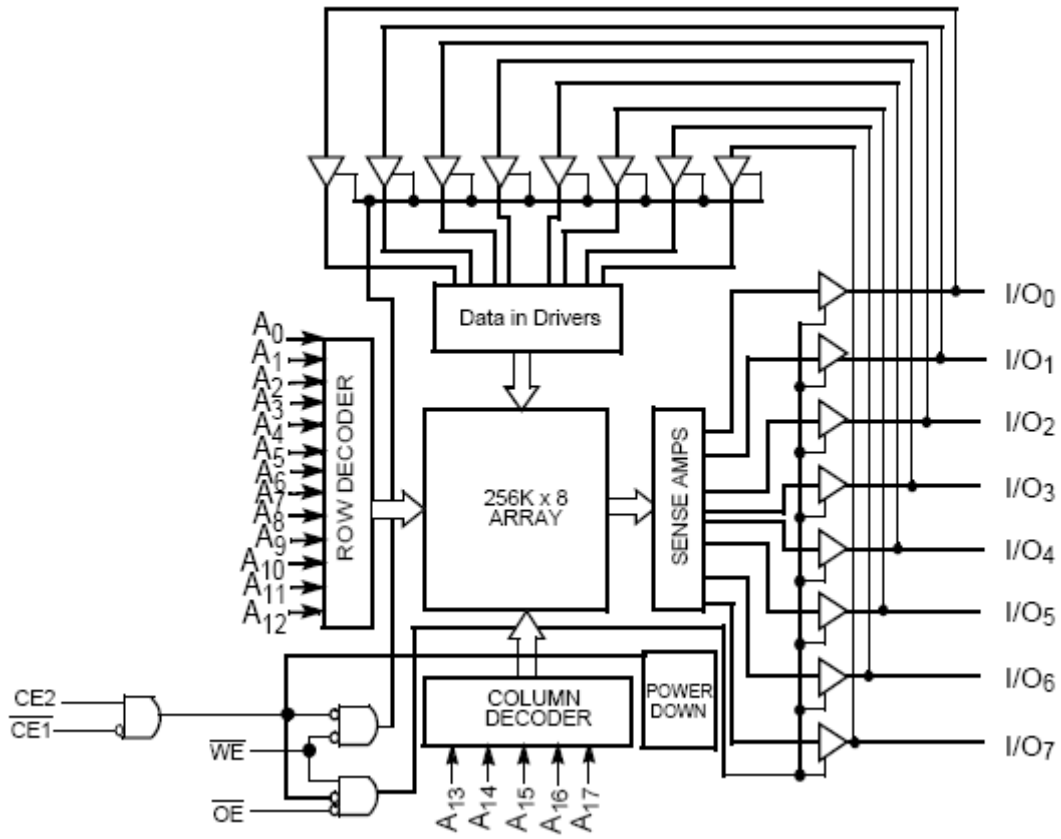
Functional Description

The M24L28256DA is a high-performance CMOS pseudo static RAM (PSRAM) organized as 256K words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable($\overline{CE}_1$) and active HIGH Chip Enable ($\overline{CE}_2$),and active LOW Output Enable ($\overline{OE}$).This device has an automatic power-down feature that reduces power consumption dramatically when deselected. Writing to the device is accomplished by asserting Chip Enable One ($\overline{CE}_1$) and Write Enable ($\overline{WE}$) inputs LOW and Chip Enable Two ($\overline{CE}_2$) input HIGH. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by asserting the Chip Enable One ($\overline{CE}_1$) and Output Enable ($\overline{OE}$) inputs LOW while forcing Write Enable ($\overline{WE}$) HIGH. And Chip Enable Two ($\overline{CE}_2$) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected ($\overline{CE}_1$ HIGH or CE_2 LOW), the outputs are disabled ($\overline{OE}$ HIGH), or during write operation ($\overline{CE}_1$ LOW, CE_2 HIGH, and $\overline{WE}$ LOW). See the Truth Table for a complete description of read and write modes.

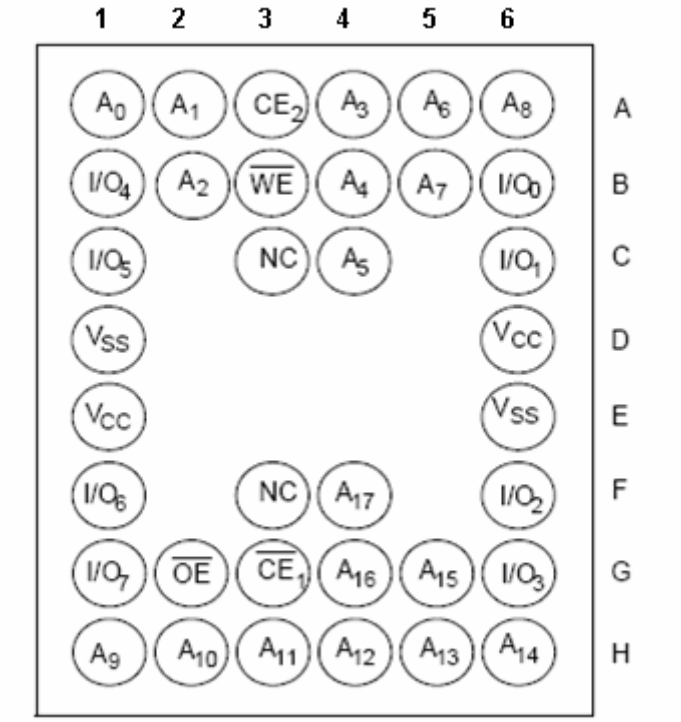
Logic Block Diagram



Pin Configuration[1]

VFBGA

Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed(ns)	Power Dissipation					
					Operating I_{CC}(mA)				Standby I_{SB2}(μA)	
					f = 1MHz		f = f_{MAX}			
	Min.	Typ.	Max.		Typ.[2]	Max.	Typ.[2]	Max.	Typ. [2]	Max.
M24L28256DA	2.7	3.0	3.3	55	1	5	14	22	9	40
				70			8	15		

Notes:
1. NC "no connect"—not connected internally to the die.
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ)}$ and T_A = 25°C.

Maximum Ratings

(Above which the useful life may be impaired. For user guide-lines, not tested.)
Storage Temperature .....–65°C to +150°C
Ambient Temperature with
Power Applied .....–40°C to +85°C
Supply Voltage to
Ground Potential . ...−0.4V to 4.6V
DC Voltage Applied to Outputs
in High-Z State[3, 4, 5] .....−0.4V to 3.7V
DC Input Voltage[3, 4, 5]..... .....−0.4V to 3.7V
Output Current into Outputs (LOW) .....20 mA

Static Discharge Voltage ..... >2001V
(per MIL-STD-883, Method 3015)
Latch-up Current .....> 200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{CC}
Extended	−25°C to +85°C	2.7V to 3.3V

Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		-55			-70			Unit
				Min.	Typ. [2]	Max.	Min.	Typ. [2]	Max.	
V_{CC}	Supply Voltage			2.7	3.0	3.3	2.7		3.3	V
V_{OH}	Output HIGH Voltage	I_{OH} = −0.1 mA		V_{CC}-0.4			V_{CC}-0.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA				0.4			0.4	V
V_{IH}	Input HIGH Voltage			0.8* V_{CC}		V_{CC}+ 0.4	0.8* V_{CC}		V_{CC} +0.4	V
V_{IL}	Input LOW Voltage			-0.4		0.4	-0.4		0.4	V
I_{IX}	Input Leakage Current	GND ≤V_{IN} ≤ V_{CC}		-1		+1	-1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC} , Output Disable		-1		+1	-1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = 3.3V I_{OUT} = 0mA CMOS levels		14	22		8	15	mA
		f = 1 MHz			1	5		1	5	
I_{SB1}	Automatic $\overline{CE}_1$ Power-Down Current —CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC}−0.2V, CE_2 ≤ 0.2V V_{IN} ≥ V_{CC} − 0.2V, V_{IN} ≤ 0.2V, f = f_{MAX} (Address and Data Only), f = 0			40	250		40	250	µA
I_{SB2}	Automatic $\overline{CE}_1$ Power-Down Current —CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC}−0.2V, CE_2 ≤ 0.2V V_{IN} ≥ V_{CC} − 0.2V, V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.3V			9	40		9	40	µA

Capacitance[6]

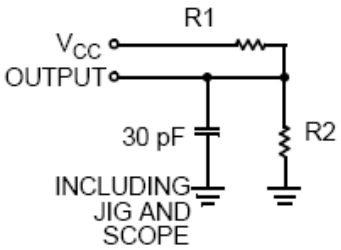
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	TA = 25°C, f = 1 MHz	8	pF
C_{OUT}	Output Capacitance	V_{CC} = $V_{CC(typ)}$	8	pF

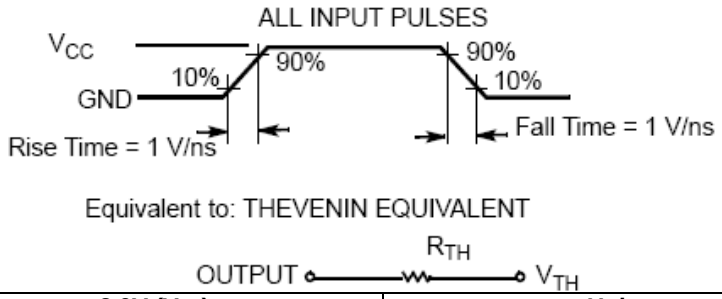
Thermal Resistance[6]

Parameter	Description	Test Conditions	BGA	Unit
Θ_{JA}	Thermal Resistance(Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/ JESD51.	55	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		17	°C/W

Notes:
3.$V_{IH(MAX)}$ = V_{CC} + 0.5V for pulse durations less than 20 ns.
4.$V_{IL(MIN)}$ = –0.5V for pulse durations less than 20 ns.
5.Overshoot and undershoot specifications are characterized and are not 100% tested.
6.Tested initially and after design or process changes that may affect these parameters.

AC Test Loads and Waveforms





Equivalent to: THEVENIN EQUIVALENT

Parameters	3.0V (V_{CC})	Unit
R1	22000	Ω
R2	22000	Ω
R_{TH}	11000	Ω
V_{TH}	1.50	V

Switching Characteristics (Over the Operating Range) [7]

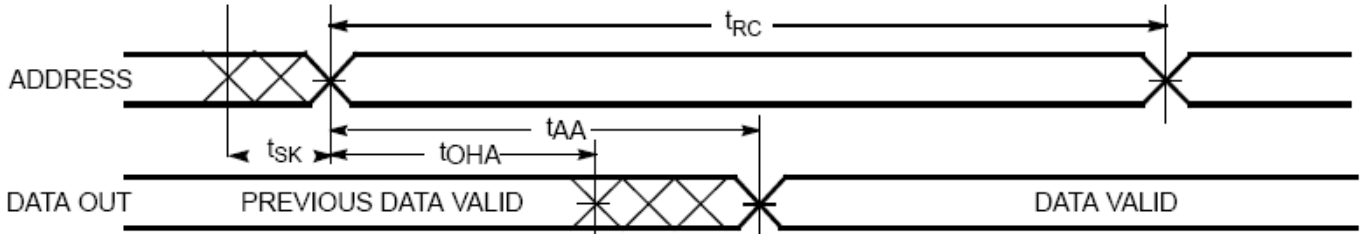
Parameter	Description	-55		-70		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{RC}	Read Cycle Time	55[11]		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	5		10		ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[8, 9]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[8, 9]		25		25	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to LOW Z[8, 9]	5		5		ns
t_{HZCE}	$\overline{CE}_1$ HIGH and CE_2 LOW to HIGH Z[8, 9]		25		25	ns
t_{SKI}11]	Address Skew		0		10	ns
Write Cycle [10]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Write End	45		55		ns
t_{AW}	Address Set-Up to Write End	45		55		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		55		ns
t_{SD}	Data Set-Up to Write End	25		25		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[8, 9]		25		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[8, 9]	5		5		ns

Notes:

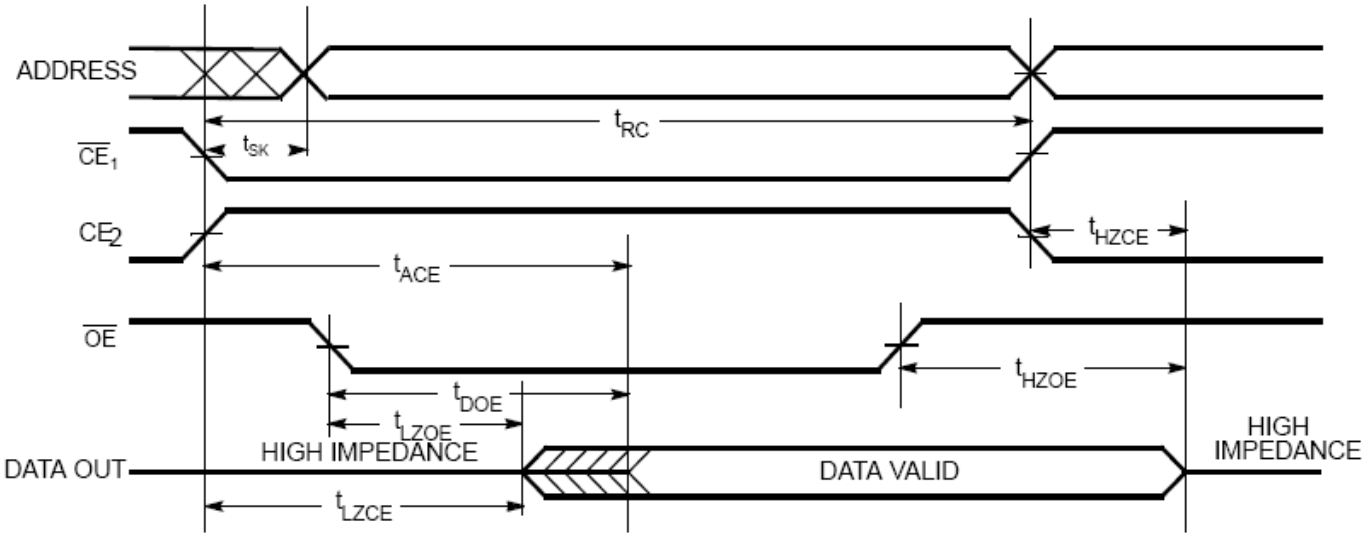
7. Test conditions assume signal transition time of 1V/ns or higher, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0V to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance
8. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
9. High-Z and Low-Z parameters are characterized and are not 100% tested.
10. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}_1$= V_{IL}, and CE_2=V_{IH} . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates write.
11. To achieve 55-ns performance, the read access should be $\overline{CE}$ controlled. In this case t_{ACE} is the critical parameter and t_{SK} is satisfied when the addresses are stable prior to chip enable going active. For the 70-ns cycle, the addresses must be stable within 10 ns after the start of the read cycle.

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[11, 12, 13]



Read Cycle 2 ($\overline{OE}$ Controlled)[11, 13]

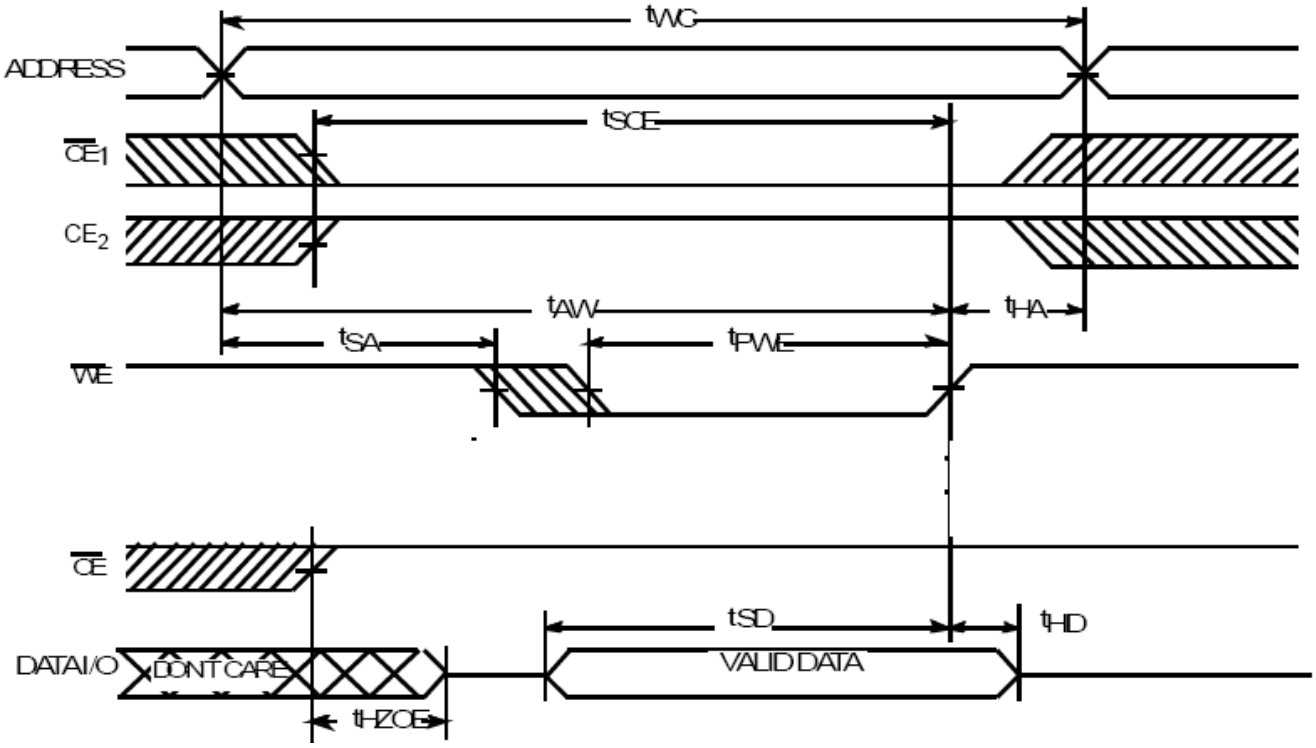


Notes:

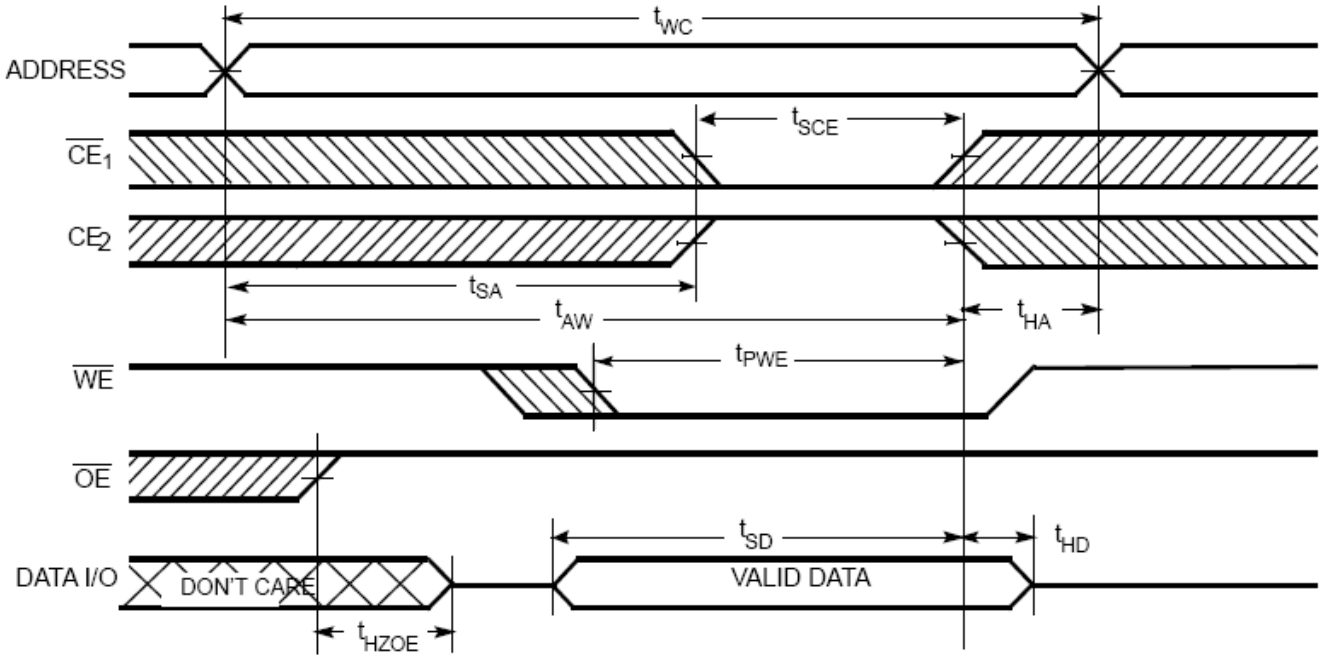
12. Device is continuously selected. $\overline{OE}$, $\overline{CE}_1$=V_{IL} and CE_2 = V_{IH}.
13. $\overline{WE}$ is HIGH for Read Cycle.

Switching Waveforms (continued)

Write Cycle No.1 ($\overline{WE}$ Controlled)[9,10, 14, 15, 16]



Write Cycle 2 ($\overline{CE}_1$ or CE_2 Controlled) [9, 10, 14, 15, 16]



Notes:

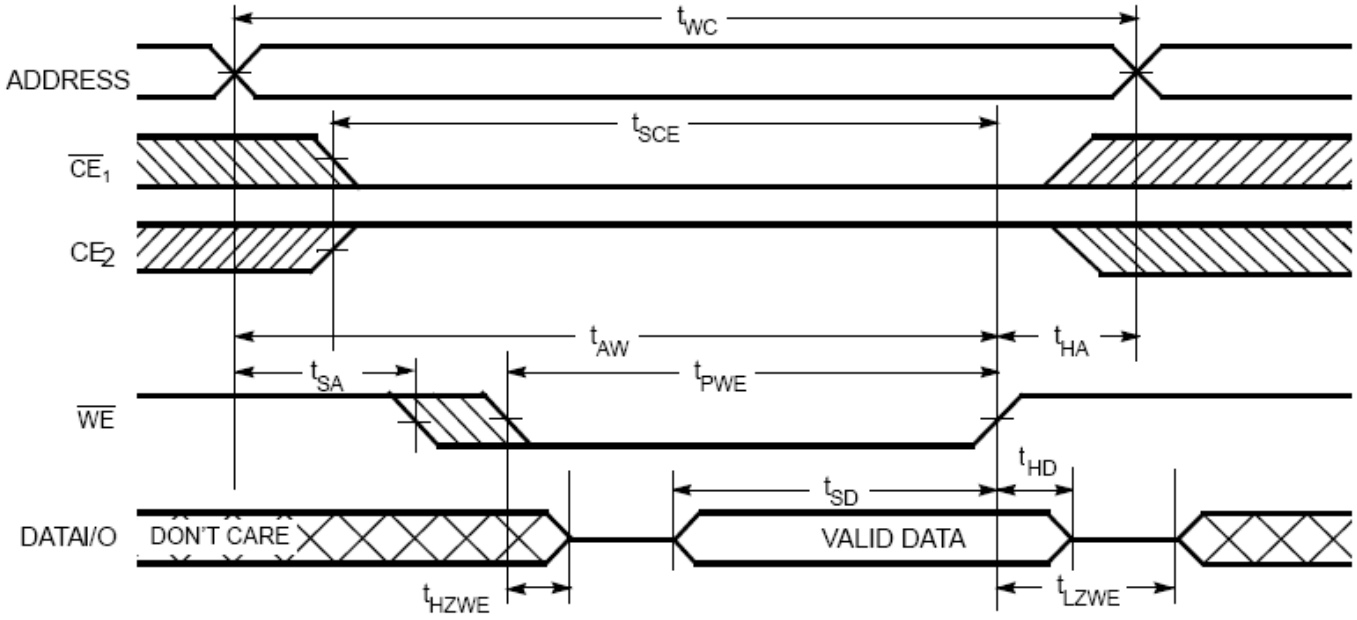
14.Data I/O is high impedance if $\overline{OE}$ ≥ V_{IH}.

15. If Chip Enables go INACTIVE simultaneously with $\overline{WE}$ =HIGH, the output remains in a high-impedance state.

16.During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[15, 16]



Truth Table[17]

$\overline{CE}_1$	CE_2	$\overline{OE}$	$\overline{WE}$	I/O_0-I/O_7	Mode	Power
H	X	X	X	High Z	Power-Down	Standby (I_{SB})
X	L	X	X	High Z	Power-Down	Standby (I_{SB})
L	H	L	H	Data Out	Read	Active (I_{CC})
L	H	X	L	Data In	Write	Active (I_{CC})
L	H	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

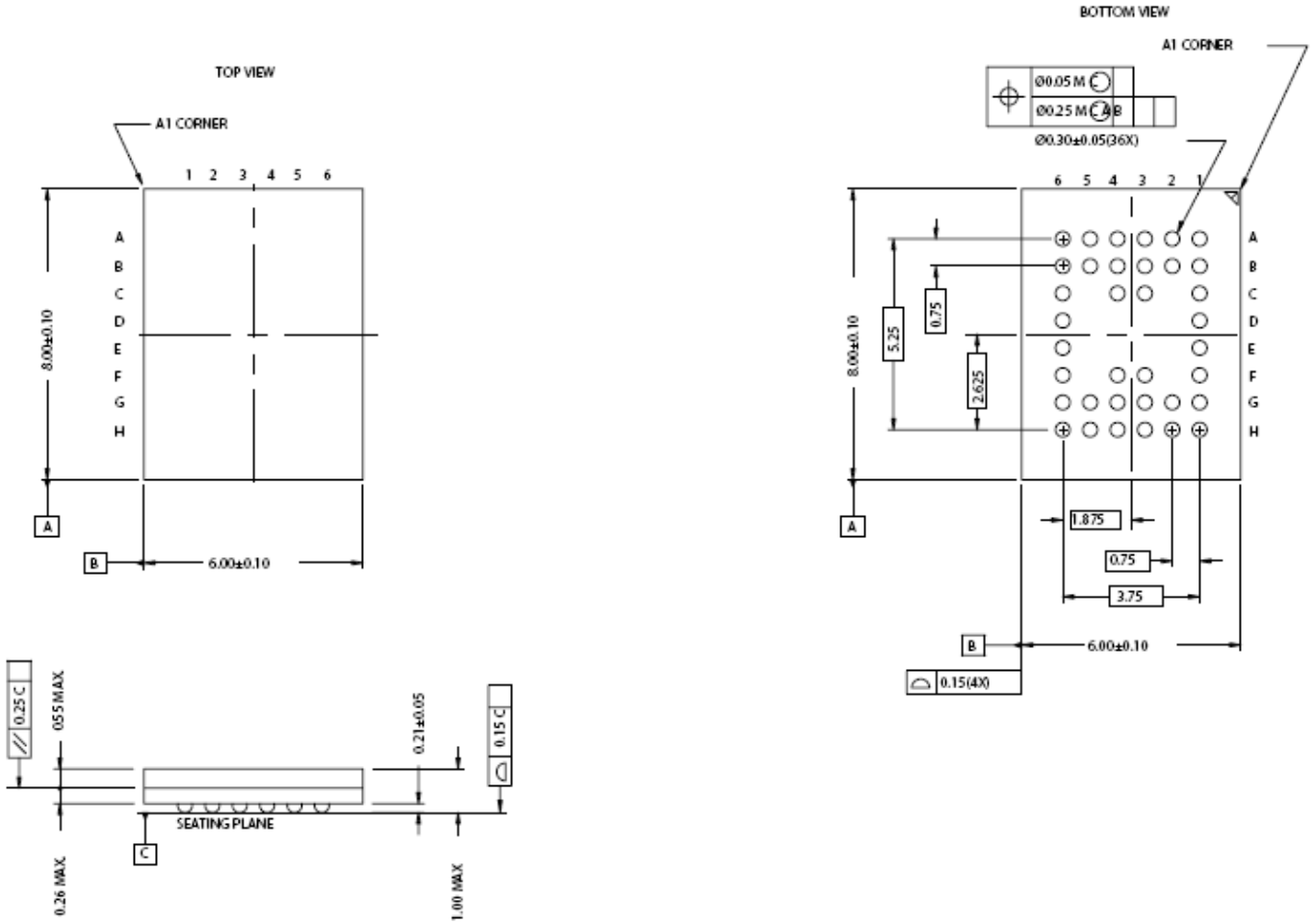
Ordering Information

Speed (ns)	Ordering Code	Package Type	Operating Range
55	M24L28256DA-55BEG	36-Lead VFBGA (6 x 8 x 1 mm) (Pb-free)	Extended
70	M24L28256DA-70BEG	36-Lead VFBGA (6 x 8 x 1 mm) (Pb-free)	Extended

Note:
17.H = Logic HIGH, L = Logic LOW, X = Don't Care.

Package Diagrams

36-Lead VFBGA (6 x 8 x 1 mm)



Revision History

Revision	Date	Description
1.0	2007.07.19	Original

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